LAPT 2SA1386/1386A

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC3519/A)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	2SA1386	2SA1386A	Unit
V_{CBO}	–160	–180	V
V_{CEO}	–160	–180	V
V_{EBO}	–5		V
I_C	–15		A
I_B	–4		A
P_C	130(Tc=25°C)		W
Tj	150		°C
Tstg	–55 to +150		°C

Electrical Characteristics (Ta=25°C)

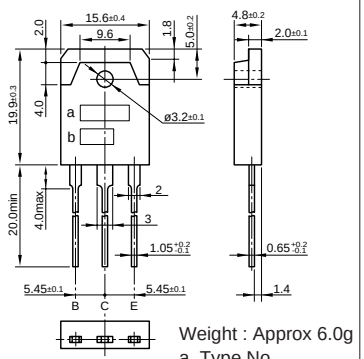
Symbol	Conditions	2SA1386	2SA1386A	Unit
I_{CBO}		–100max	–100max	μA
	V_{CB}=	–160	–180	V
I_{EBO}	V_{EB}=–5V	–100max		μA
$V_{(BR)CEO}$	I_C=–25mA	–160min	–180min	V
h_{FE}	V_{CE}=–4V, I_C=–5A	50min*		
$V_{CE(sat)}$	I_C=–5A, I_B=–0.5A	–2.0max		V
f_T	V_{CE}=–12V, I_E=2A	40typ		MHz
C_{OB}	V_{CB}=–10V, f=1MHz	500typ		pF

*h_{FE} Rank O(50 to 100), P(70 to 140), Y(90 to 180)

Typical Switching Characteristics (Common Emitter)

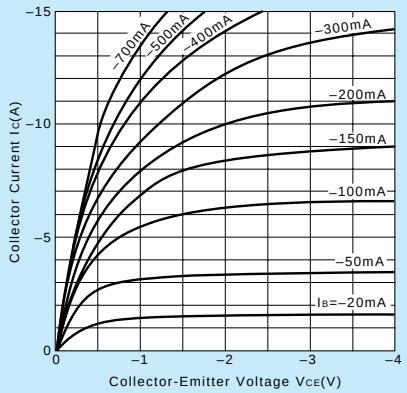
V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (A)	I_{B2} (A)	ton (μs)	tstg (μs)	tf (μs)
–40	4	–10	–10	5	–1	1	0.3typ	0.7typ	0.2typ

External Dimensions MT-100(TO3P)

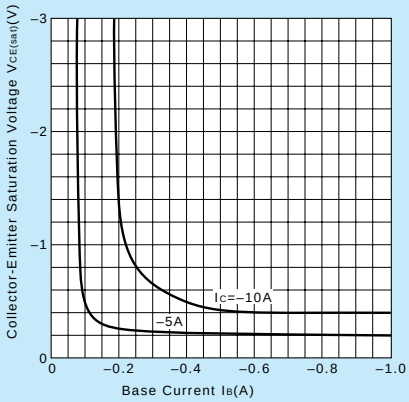


Weight : Approx 6.0g
a. Type No.
b. Lot No.

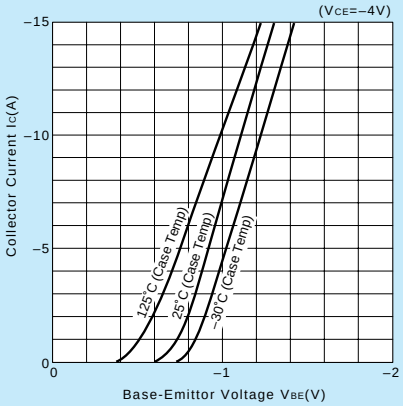
I_C–V_{CE} Characteristics (Typical)



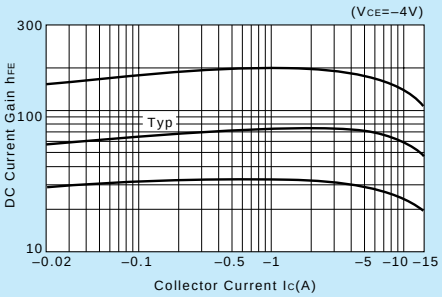
$V_{CE(sat)}$–I_B Characteristics (Typical)



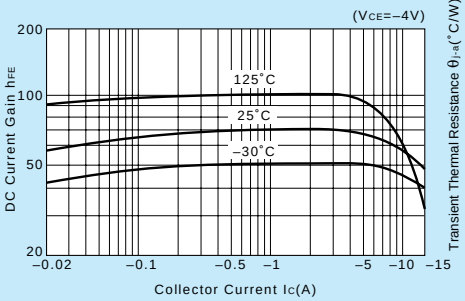
I_C–V_{BE} Temperature Characteristics (Typical)



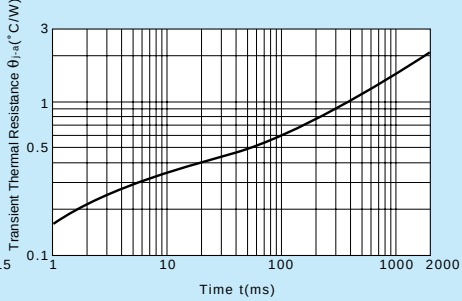
h_{FE}–I_C Characteristics (Typical)



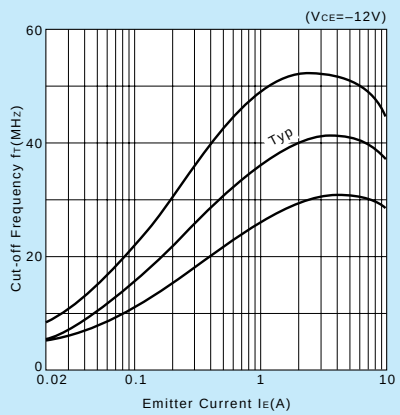
h_{FE}–I_C Temperature Characteristics (Typical)



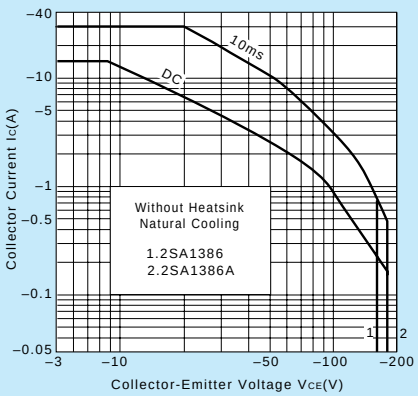
$\theta_{j\text{-}a}$–t Characteristics



f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc–Ta Derating